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FQA46N15

May 2014

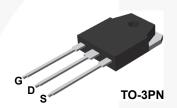
N-Channel QFET $^{\circledR}$ MOSFET 150 V, 50 A, 42 m Ω

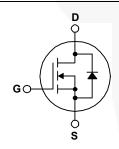
Features

- 50 A, 150 V, $R_{DS(on)}$ = 42 m Ω (Max) @ V_{GS} = 10 V, I_D = 25 A
- Low Gate Charge (Typ. 85 nC)
- Low Crss (Typ. 100 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA46N15	Unit	
V _{DSS}	Drain-Source Voltage		150	V	
I _D	Drain Current - Continuous (T _C = 25°C)		50	Α	
	- Continuous (T _C = 100°C)		35.3	Α	
I _{DM}	Drain Current - Pulsed	(Note 1)	200	Α	
V_{GSS}	Gate-Source Voltage		± 25	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		650	mJ	
I _{AR}	Avalanche Current	(Note 1)	50	A	
E _{AR}	Repetitive Avalanche Energy (Note 1)		25	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns	
P _D	Power Dissipation (T _C = 25°C)		250	W	
	- Derate above 25°C		1.67	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	°C		

Thermal Characteristics

Symbol	Parameter	FQA46N15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.6	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA46N15	FQA46N15	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					I.
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{D} = 250 μ A	150			V
$\Delta BV_{DSS}/$ ΔT_J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.16		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 150 V, V _{GS} = 0 V	1		1	μА
		V _{DS} = 120 V, T _C = 150°C	-		10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$	1		100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V	-		-100	nA
On Charact	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 25A	-	0.033	0.042	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 25A	-	36		S
Dynamic Cl	haracteristics				1	
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,	\	2500	3250	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		520	670	pF
C _{rss}	Reverse Transfer Capacitance			100	130	pF
	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 75 V, I _D = 45.6A,		35	80	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		320	650	ns
t _{d(off)}	Turn-Off Delay Time			210	430	ns
t _f	Turn-Off Fall Time	(Note 4)		200	410	ns
Qg	Total Gate Charge	V _{DS} = 120 V, I _D = 45.6A,	/	85	110	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	-/	15		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	-	41		nC
Drain-Source	ce Diode Characteristics and Maximum Ratings				/	I.
I _S Maximum Continuous Drain-Source Diode Forward Current					50	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		-		200	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S =50A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 45.6 A,	-	130		ns
Q _{rr}	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$		0.55		μС

NOTES

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 0.43 mH, I $_{AS}$ = 50 A, V $_{DD}$ = 25 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$

 $^{3.}I_{SD} \leq 46.6 \text{ A, di/dt} \leq 300 \text{ A/}\mu\text{s, V}_{DD} \leq BV_{DSS}\text{, starting T}_J = 25^{\circ}C.$

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

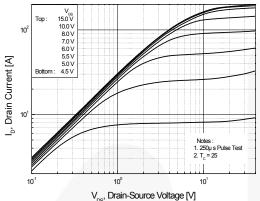
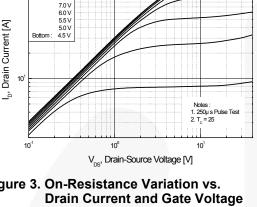


Figure 3. On-Resistance Variation vs.



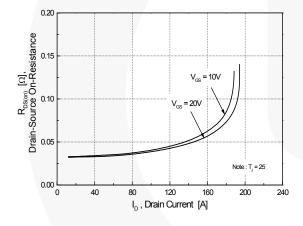


Figure 5. Capacitance Characteristics

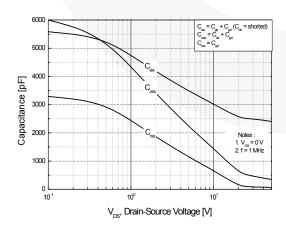


Figure 2. Transfer Characteristics

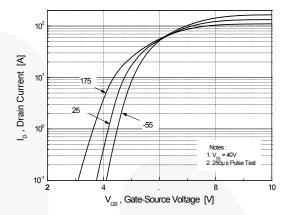


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

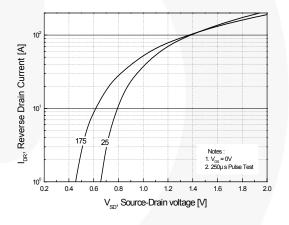
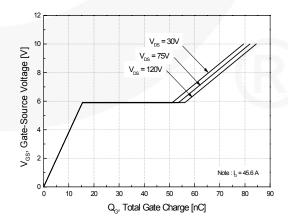


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

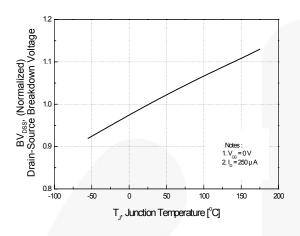


Figure 8. On-Resistance Variation vs. Temperature

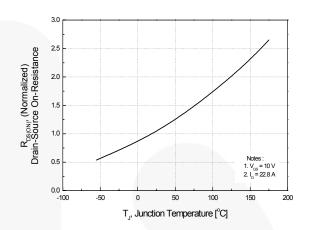


Figure 9. Maximum Safe Operating Area

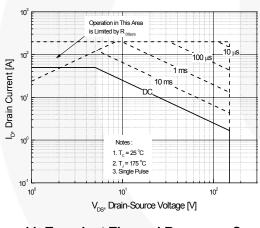


Figure 10. Maximum Drain Current vs. Case Temperature

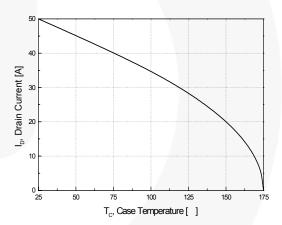
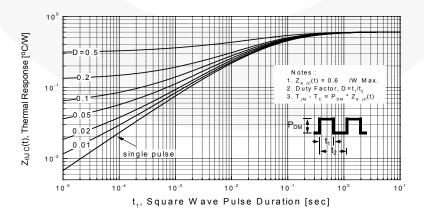


Figure 11. Transient Thermal Response Curve



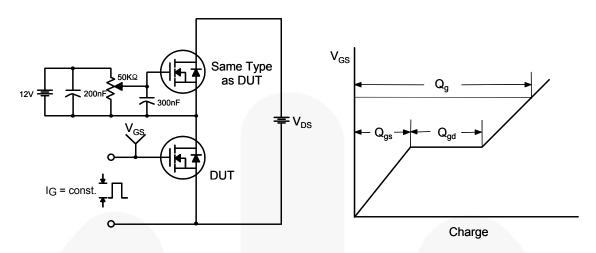


Figure 12. Gate Charge Test Circuit & Waveform

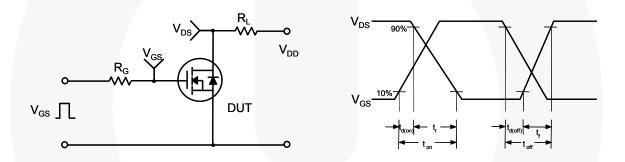


Figure 13. Resistive Switching Test Circuit & Waveforms

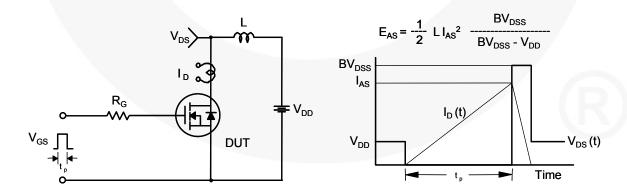


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

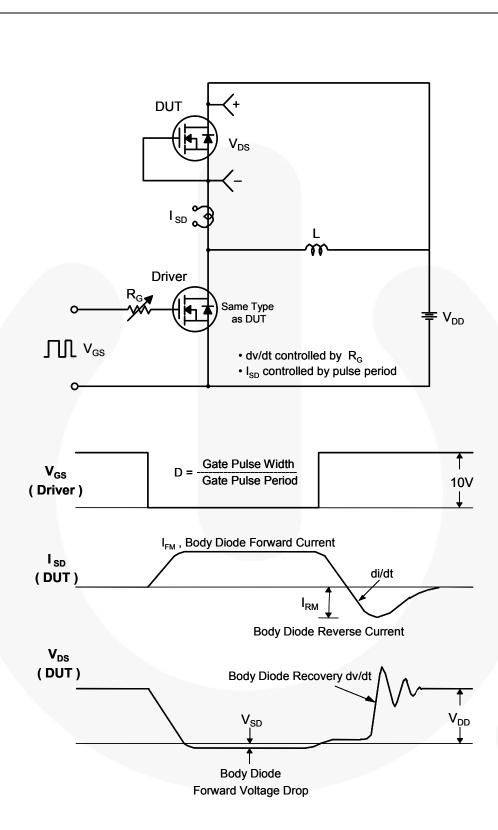
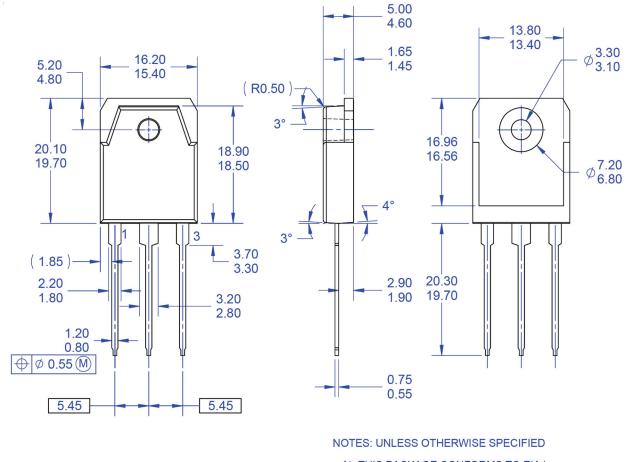
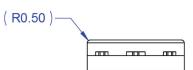


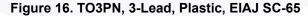
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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